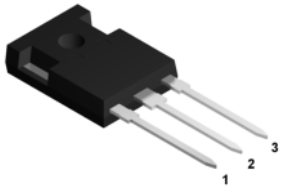
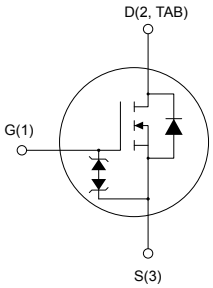
STWA72N60DM2AG

Datasheet

Automotive-grade N-channel 600 V, 37 mΩ typ., 66 A MDmesh DM2 Power MOSFET in a TO-247 long leads package



TO-247 long leads



AM01476v1_tab

Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STWA72N60DM2AG	600 V	42 mΩ	66 A

- AEC-Q101 qualified
- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM2 fast-recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high-efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Product status link
STWA72N60DM2AG

Product summary	
Order code	STWA72N60DM2AG
Marking	72N60DM2
Package	TO-247 long leads
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	66	A
	Drain current (continuous) at T_C = 100 °C	42	
I_{DM}(1)	Drain current (pulsed)	220	A
P_{TOT}	Total dissipation at T_{case} = 25 °C	446	W
dv/dt(2)	Peak diode recovery voltage slope	50	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width is limited by safe operating area.*
2. *I_{SD} ≤ 66 A, V_{DS} (peak) < $V_{(BR)DSS}$, di/dt = 800 A/µs, V_{DD} = 480 V.*
3. *V_{DS} ≤ 480 V*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.28	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_J max.)	8	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	1500	mJ

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			10	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C (1)			100	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 33 A		37	42	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	5508	-	pF
C_{oss}	Output capacitance		-	241	-	pF
C_{rss}	Reverse transfer capacitance		-	2.8	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	470	-	pF
R_g	Intrinsic gate resistance	f = 1 MHz open drain	-	2	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 66 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	121	-	nC
Q_{gs}	Gate-source charge		-	26	-	nC
Q_{gd}	Gate-drain charge		-	61	-	nC

1. *$C_{oss\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to stated value.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 33 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	32	-	ns
t_r	Rise time		-	67	-	ns
$t_{d(off)}$	Turn-off delay time		-	112	-	ns
t_f	Fall time		-	10.4	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		66	A
I_{SDM}(1)	Source-drain current (pulsed)		-		220	A
V_{SD}(2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 66 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 66 A, di/dt = 100 A/µs, V_{DD} = 480 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	150		ns
Q_{rr}	Reverse recovery charge		-	0.75		µC
I_{RRM}	Reverse recovery current		-	10.5		A
t_{rr}	Reverse recovery time	I_{SD} = 66 A, di/dt = 100 A/µs, V_{DD} = 480 V, T_j = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	250		ns
Q_{rr}	Reverse recovery charge		-	2.5		µC
I_{RRM}	Reverse recovery current		-	20.7		A

1. *Pulse width is limited by safe operating area.*
2. *Pulse test: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

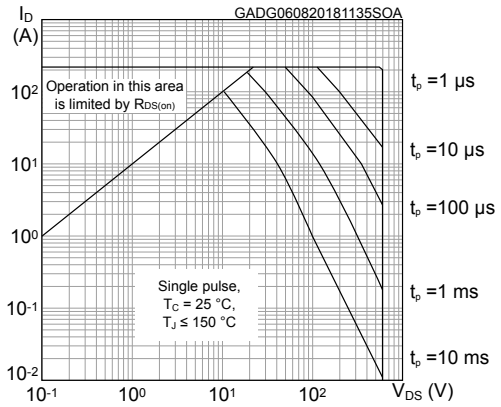


Figure 2. Normalized transient thermal impedance

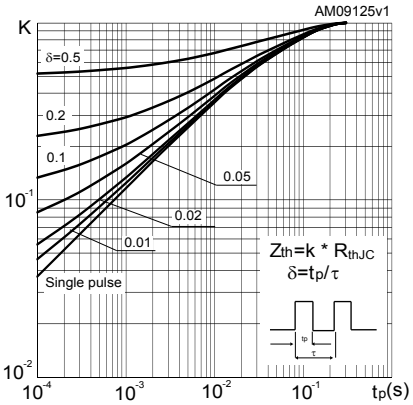


Figure 3. Tipical output characteristics

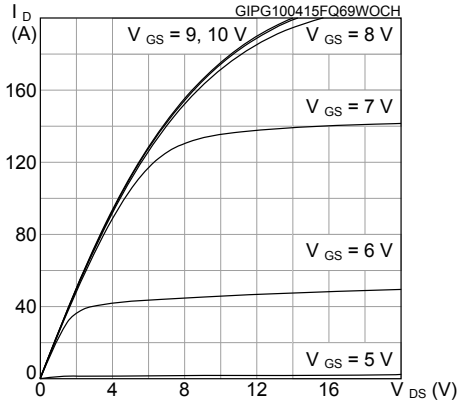


Figure 4. Tipical transfer characteristics

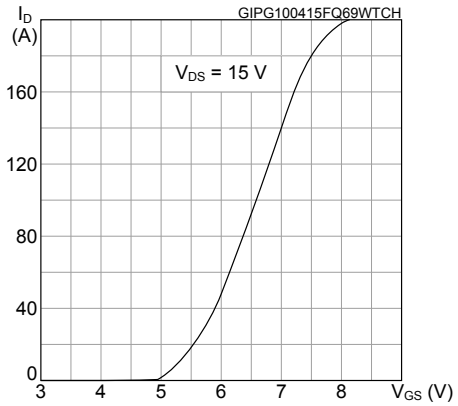


Figure 5. Typical gate charge characteristics

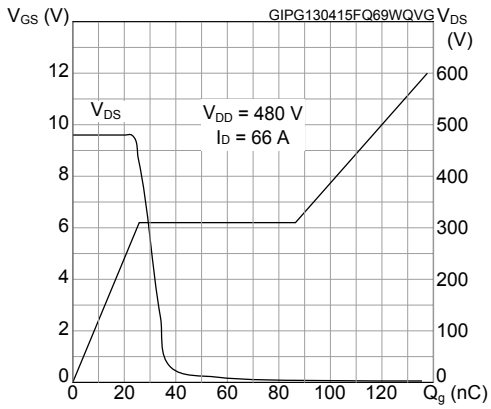


Figure 6. Typical drain-source on-resistance

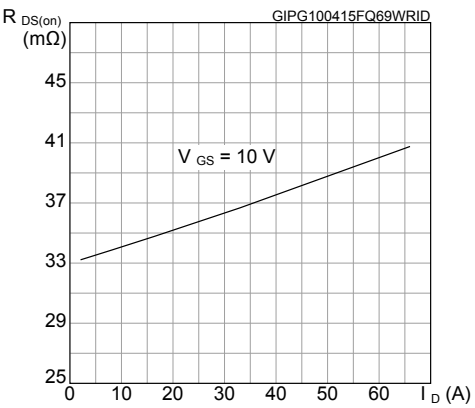


Figure 7. Typical capacitance characteristics

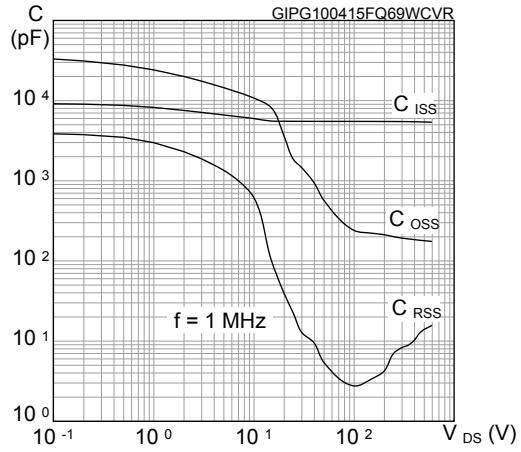


Figure 8. Normalized gate threshold vs temperature

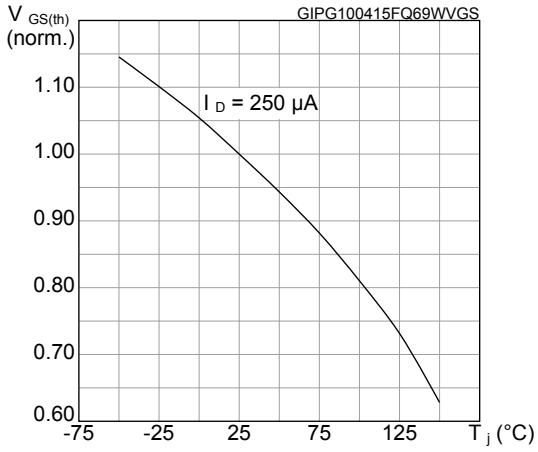


Figure 9. Normalized on-resistance vs temperature

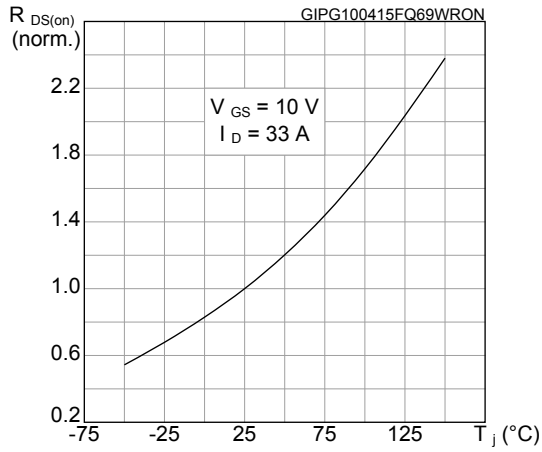


Figure 10. Normalized breakdown voltage vs temperature

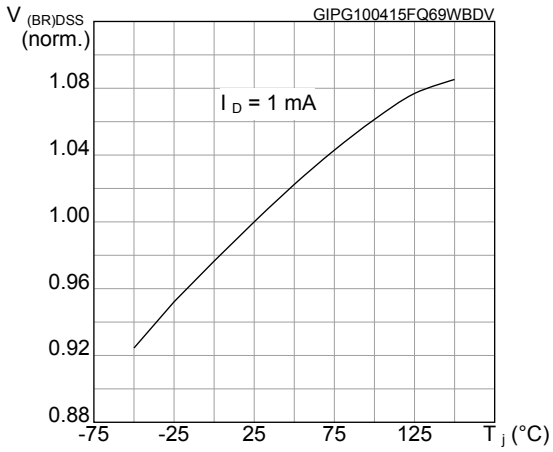


Figure 11. Typical output capacitance stored energy

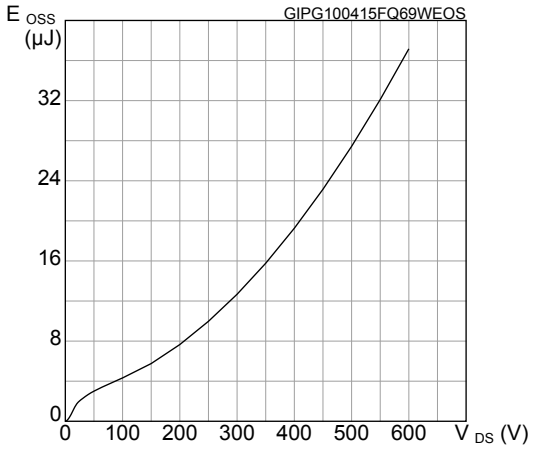
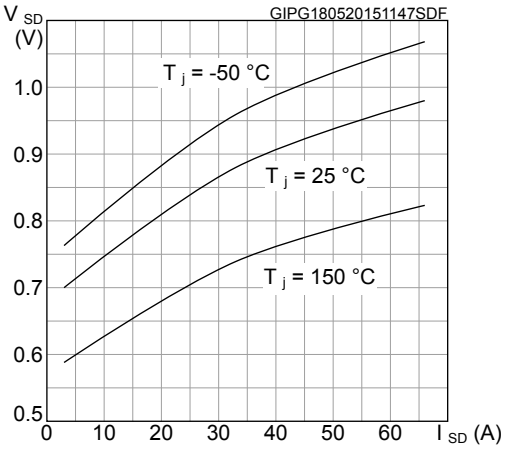
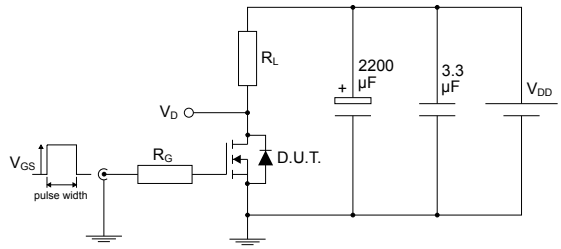


Figure 12. Typical reverse diode forward characteristics



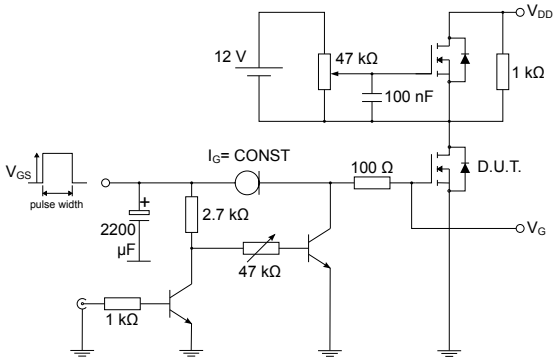
3 Test circuits

Figure 13. Test circuit for resistive load switching times



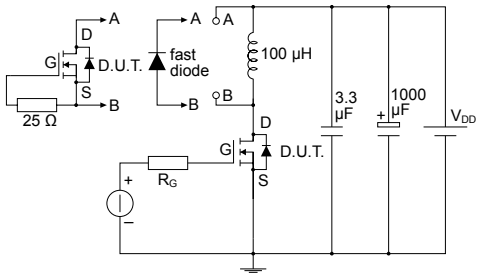
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Figure 14. Test circuit for gate charge behavior



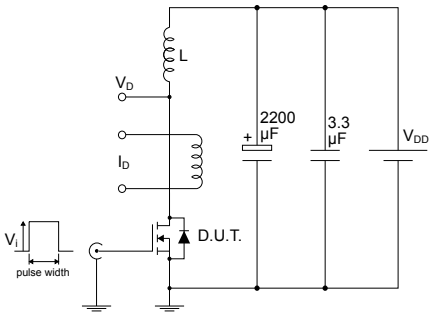
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Figure 15. Test circuit for inductive load switching and diode recovery times



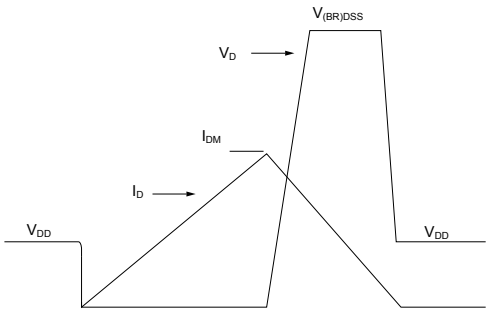
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Figure 16. Unclamped inductive load test circuit



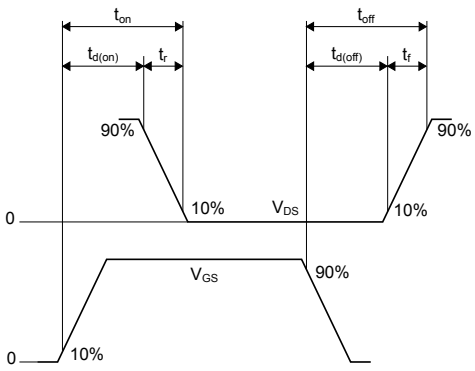
AM01471v1

Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1

4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 long leads package information

Figure 19. TO-247 long leads package outline

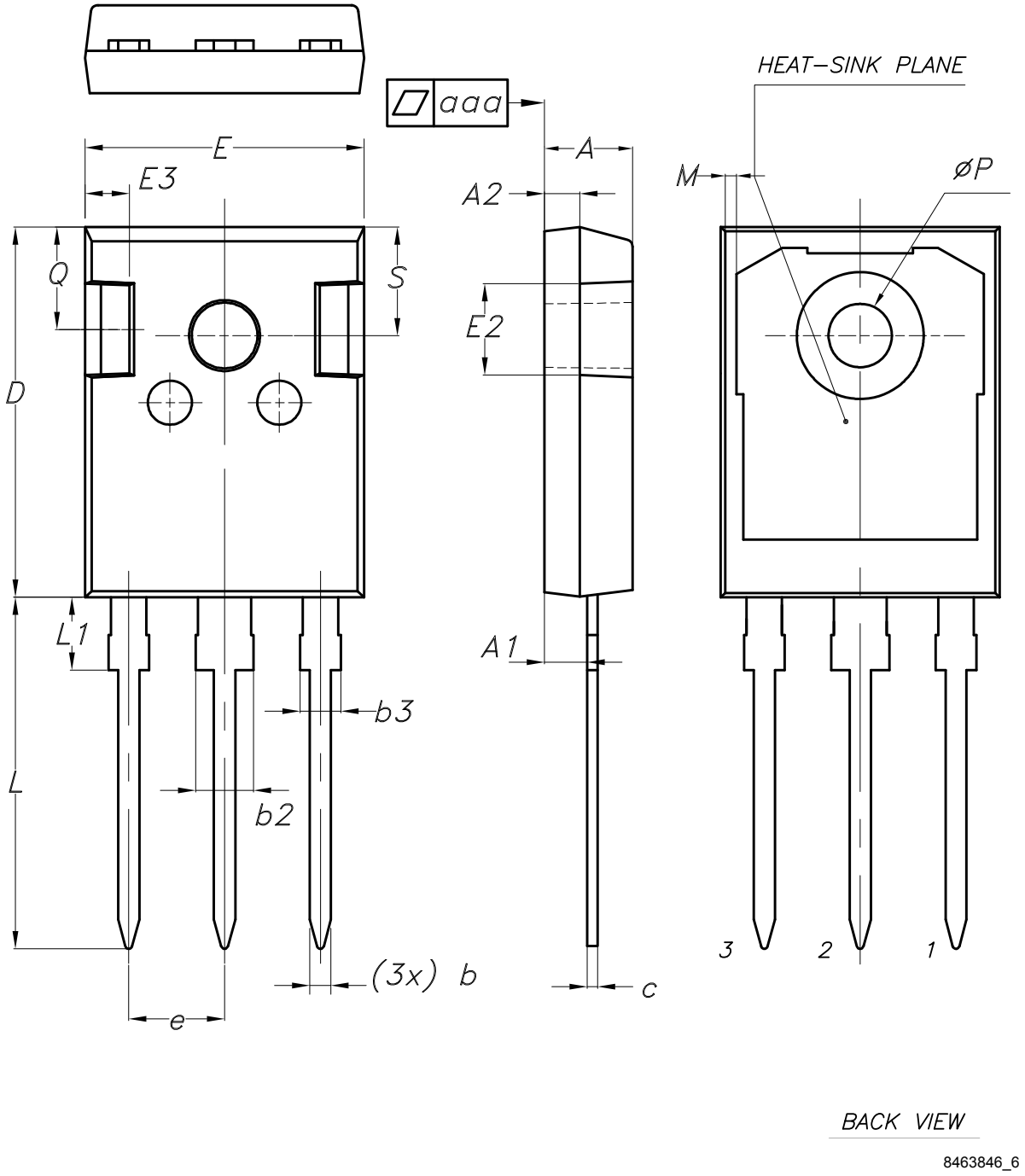


Table 8. **TO-247 long leads package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
M	0.35		0.95
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25
aaa		0.04	0.10

Revision history

Table 9. **Document revision history**

Date	Version	Changes
07-Aug-2018	1	Initial release. The document status is production data.
20-Mar-2025	2	Updated Section 4.1: TO-247 long leads package information. Minor text changes.

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